TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIV)

TPCF8003

Notebook PC Applications Portable Equipment Applications

· Small footprint due to small and thin package

• Low drain-source ON-resistance: RDS (ON) =14 m Ω (typ.) (VGS= 4.5V)

• Low leakage current: $IDSS = 10 \mu A (max) (VDS = 20 V)$

 \bullet $\;$ Enhancement mode: V_{th} = 0.5 to 1.2 V

 $(V_{DS} = 10 \text{ V}, I_{D} = 200 \mu\text{A})$

Absolute Maximum Ratings (Ta = 25°C)

| Characte | ristics | Symbol | Rating | Unit | |
|---|---------------------------|------------------|------------|------|--|
| Drain-source voltage | | V_{DSS} | 20 | V | |
| Drain-gate voltage (R | GS = 20 kΩ) | V_{DGR} | 20 | V | |
| Gate-source voltage | | V _{GSS} | ±12 | V | |
| Drain current | DC (Note 1) | I _D | 7 | А | |
| | Pulse (Note 1) | I _{DP} | 28 | | |
| Drain power dissipation | on (t = 5 s) (Note 2a) | P _D | 2.5 | W | |
| Drain power dissipation (t = 5 s) (Note 2b) | | P _D | 0.7 | W | |
| Single pulse avalanch | ne energy (Note 3) | E _{AS} | 3.2 | mJ | |
| Avalanche current | | I _{AR} | 3.5 | Α | |
| Channel temperature | | T _{ch} | 150 | °C | |
| Storage temperature | range | T _{stg} | -55 to 150 | °C | |

Unit: mm 0.8 ± 0.05 ____0.05|S Α 0.71+0.0 0.24+0.10 86 0.475 5.Source 1 Drain 2. Drain 6. Drain 3. Drain 7. Drain 4. Gate 8. Drain JEDEC JEITA **TOSHIBA** 2-3U1A

Weight: 0.011 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

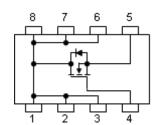
Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|--|------------------------|-------|------|
| Thermal resistance, channel to ambient (t = 5 s) (Note 2a) | R _{th (ch-a)} | 50.0 | °C/W |
| Thermal resistance, channel to ambient (t = 5 s) (Note 2b) | R _{th (ch-a)} | 178.6 | °C/W |

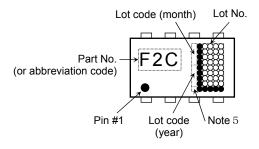
Note: For Notes 1 to 3, refer to the next page.

This transistor is an electrostatic-sensitive device. Please handle with caution.

Circuit Configuration



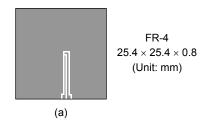
Marking (Note 4)

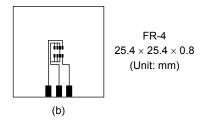


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3: V_{DD} = 16 V, T_{ch} = 25°C (initial), L = 0.2 mH, R_G = 25 Ω , I_{AR} = 3.5 A

Note 4: • on lower left of the marking indicates Pin 1.

Note 5: A dot marking for identifying the indication of product Labels. Without a dot: [[Pb]]/INCLUDES > MCV

With a dot: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

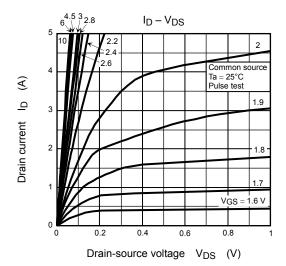
Electrical Characteristics (Ta = 25°C)

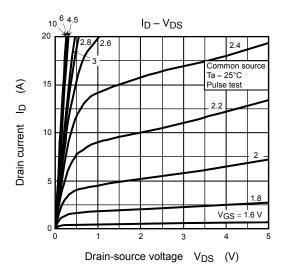
| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------------------|-----------------------|--|-----|------|------|------|
| Gate leakage cui | leakage current | | $V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±100 | nA |
| Drain cut-off curr | ent | I _{DSS} | V _{DS} = 20 V, V _{GS} = 0 V | _ | _ | 10 | μА |
| Drain-source breakdown voltage | | V _{(BR) DSS} | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$ 20 | | _ | _ | V |
| | | V _{(BR) DSX} | $I_D = 10 \text{ mA}, V_{GS} = -12 \text{ V}$ | 8 | _ | _ | V |
| Gate threshold v | oltage | V _{th} | $V_{DS} = 10 \text{ V}, I_D = 200 \mu\text{A}$ | 0.5 | _ | 1.2 | V |
| Drain-source ON-resistance | | _ | V _{GS} = 2.5 V, I _D = 3.5 A | _ | 24 | 34 | - mΩ |
| | | R _{DS} (ON) | V _{GS} = 4.5 V, I _D = 3.5 A | _ | 14 | 18 | |
| Input capacitance | | C _{iss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | _ | 500 | _ | pF |
| Reverse transfer | Reverse transfer capacitance | | | _ | 155 | _ | |
| Output capacitance | | Coss | | _ | 215 | _ | |
| Switching time | Rise time | t _r | $V_{GS} \stackrel{5}{\underset{0}{\bigvee}} I_{D} = 3.5 \text{ A}$ | _ | 5.2 | _ | ns |
| | Turn-on time | t _{on} | i ± 1 ~ | _ | 11 | _ | |
| | Fall time | t _f | 8. H | _ | 10 | _ | |
| | Turn-off time | t _{off} | V _{DD} ≈ 10 V Duty ≤ 1%, t _w = 10 μs | _ | 23 | _ | |
| Total gate charge (gate-source plus gate-drain) | | Qg | | _ | 9.5 | _ | nC |
| Gate-source charge 1 | | Q _{gs1} | $V_{DD} \approx 16 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 7.0 \text{ A}$ | _ | 1.6 | | |
| Gate-drain ("miller") charge | | Q _{gd} | | _ | 4 | _ | |

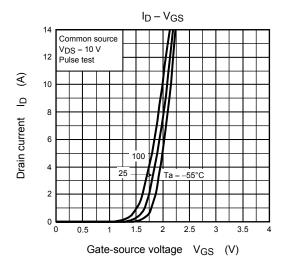
Source-Drain Ratings and Characteristics (Ta = 25°C)

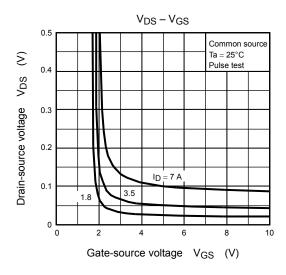
| Characteristics Symbol | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|------------------------|---|------------------|--|-----|------|------|------|
| Drain reverse current | Pulse (Note 1) | I _{DRP} | _ | _ | _ | 28 | Α |
| Forward voltage | orward voltage (diode) V _{DSF} | | I _{DR} = 7.0 A, V _{GS} = 0 V | | _ | -1.2 | V |

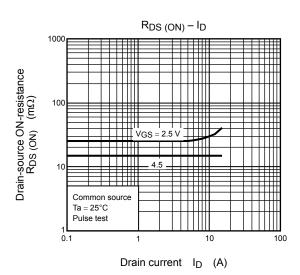
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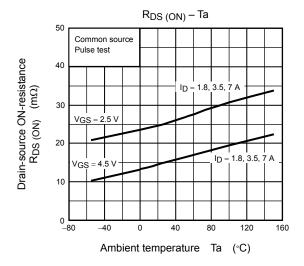


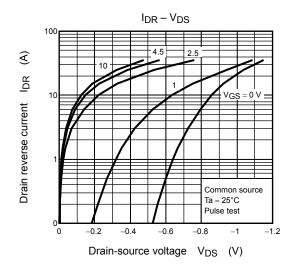


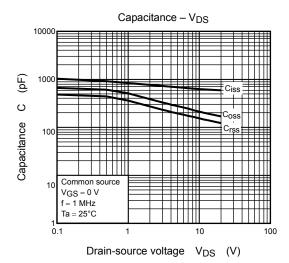


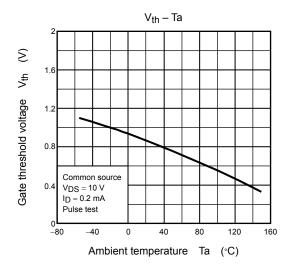


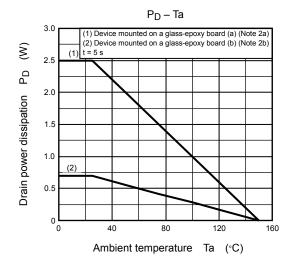


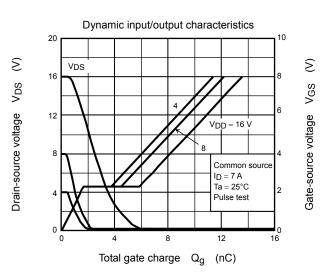




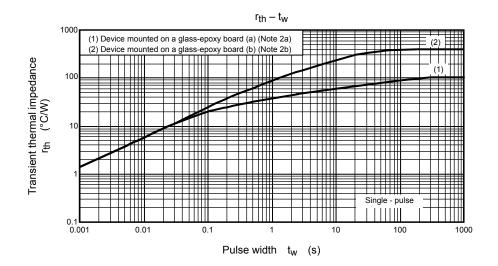


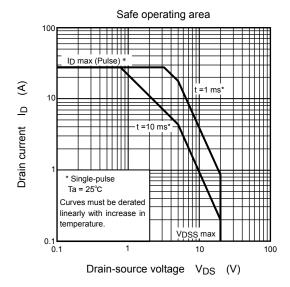






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